

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1538-8** is a Common Base Device Designed for DME IFF, and TACAN Pulse Applications.

FEATURES INCLUDE:

- Gold Metelization
- InputMatching
- Broad Band Performance

MAXIMUM RATINGS

I_C	11 A
V_{CES}	65 V
P_{DISS}	583 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	0.30 °C/W

PACKAGE STYLE 400 2L FLG (A)

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.135 / 3.43	.145 / 3.68
B	.100 / 2.54	.120 / 3.05
C	.050 / 1.27	
D	.376 / 9.55	.396 / 10.06
E	.110 / 2.79	.130 / 3.30
F	.395 / 10.03	.407 / 10.34
G	.193 / 4.90	
H	.490 / 12.45	.510 / 12.95
I	.100 / 2.54	
J	.690 / 17.53	.710 / 18.03
K	.890 / 22.61	.910 / 23.11
L	.003 / 0.08	.006 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.118 / 3.00	.131 / 3.33
P		.230 / 5.84

CHARACTERISTICS T_C = 25°C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 25 mA	65			V
BV_{CBO}	I _C = 10 mA	65			V
BV_{EBO}	I _E = 5.0 mA	3.5			V
I_{CEO}	V _{CE} = 50 V			10	mA
h_{FE}	V _{CE} = 5.0 V I _C = 300 mA	5.0			---
P_{OUT}	V _{CC} = 50 V P _{IN} = 25 W f = 1025 to 1150 MHz	150			W
G_p	PULSE WIDTH = 10 μS DUTY CYCLE = 1.0%	8.2			dB